Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	BC556 BC557 BC558	V _{CEO}	-65 -45 -30	Vdc
Collector - Base Voltage	BC556 BC557 BC558	V _{CBO}	-80 -50 -30	Vdc
Emitter - Base Voltage		V _{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak		I _C	-100 -200	mAdc
Base Current – Peak		I _{BM}	-200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C		P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range		T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

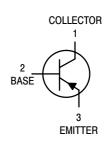
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

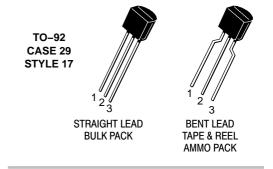
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



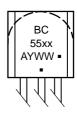
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MARKING DIAGRAM



xx = 6B, 7A, 7B, 7C, or 8B A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = -2.0 mAdc, I _B = 0)	BC556 BC557 BC558	V _{(BR)CEO}	-65 -45 -30	- - -	- - -	V
Collector – Base Breakdown Voltage (I _C = –100 μAdc)	BC556 BC557 BC558	V _(BR) CBO	-80 -50 -30	- - -	- - -	V
Emitter – Base Breakdown Voltage ($I_E = -100 \mu Adc$, $I_C = 0$)	BC556 BC557 BC558	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	- - -	- - -	V
Collector–Emitter Leakage Current (V _{CES} = -40 V) (V _{CES} = -20 V) (V _{CES} = -20 V, T _A = 125°C)	BC556 BC557 BC558 BC556	I _{CES}	- - -	-2.0 -2.0 -2.0	-100 -100 -100 -4.0	nA μA
	BC557 BC558		_	_	-4.0 -4.0	
ON CHARACTERISTICS						
DC Current Gain $(I_C = -10 \ \mu Adc, \ V_{CE} = -5.0 \ V)$ $(I_C = -2.0 \ mAdc, \ V_{CE} = -5.0 \ V)$	A Series Device B Series Devices C Series Devices BC557 A Series Device B Series Devices	h _{FE}	- - 120 120 180	90 150 270 - 170 290	- - 800 220 460	_
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ V})$	C Series Devices A Series Device B Series Devices C Series Devices		420 - - -	500 120 180 300	800 - - -	
Collector – Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc) (I _C = -10 mAdc, I _B = see Note 1) (I _C = -100 mAdc, I _B = -5.0 mAdc)		V _{CE(sat)}	- - -	-0.075 -0.3 -0.25	-0.3 -0.6 -0.65	V
Base – Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc)		V _{BE(sat)}	- -	-0.7 -1.0	<u>-</u>	V
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	-0.55 -	-0.62 -0.7	-0.7 -0.82	V
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 V, f = 100 MHz)	BC556 BC557 BC558	f _T	- - -	280 320 360	- - -	MHz
Output Capacitance $(V_{CB} = -10 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz})$		C_{ob}	-	3.0	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz, Δ f = 200 Hz)	BC556 BC557 BC558	NF	- - -	2.0 2.0 2.0	10 10 10	dB
Small–Signal Current Gain ($I_C = -2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC557 A Series Device B Series Devices C Series Devices	h _{fe}	125 125 240 450	- - - -	900 260 500 900	-

^{1.} $I_C = -10$ mAdc on the constant base current characteristics, which yields the point $I_C = -11$ mAdc, $V_{CE} = -1.0$ V.

BC557/BC558

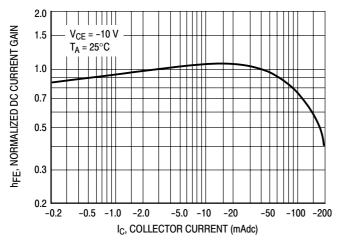


Figure 1. Normalized DC Current Gain

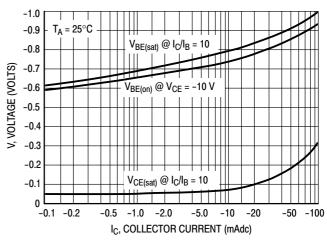


Figure 2. "Saturation" and "On" Voltages

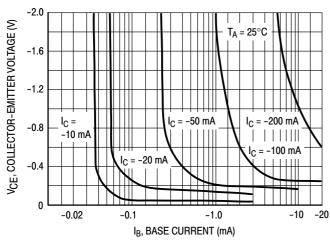


Figure 3. Collector Saturation Region

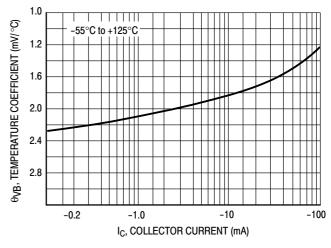


Figure 4. Base-Emitter Temperature Coefficient

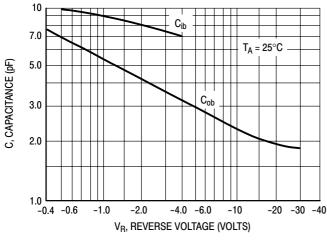


Figure 5. Capacitances

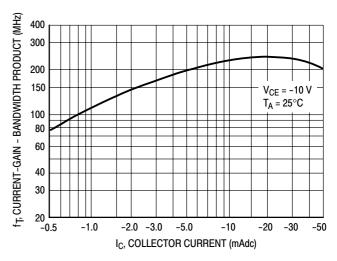


Figure 6. Current-Gain - Bandwidth Product

BC556

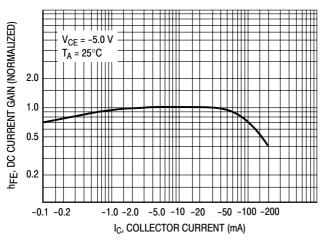


Figure 7. DC Current Gain

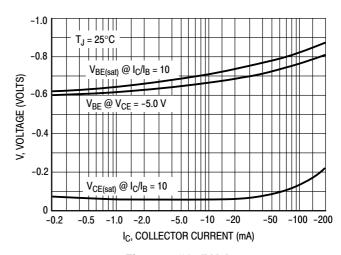


Figure 8. "On" Voltage

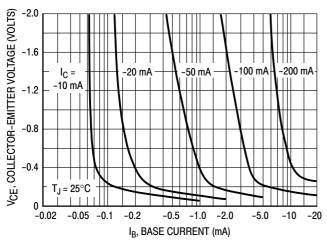


Figure 9. Collector Saturation Region

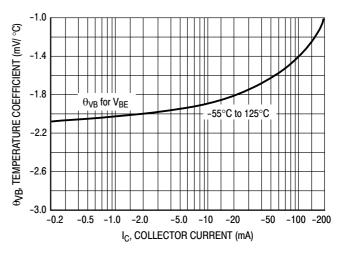


Figure 10. Base-Emitter Temperature Coefficient

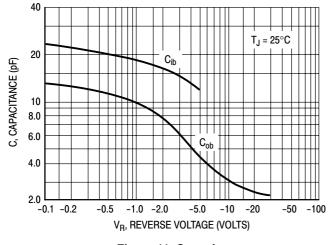


Figure 11. Capacitance

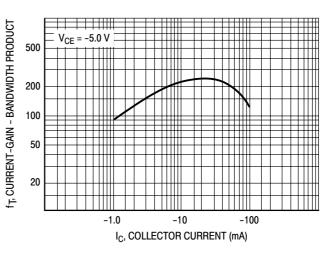


Figure 12. Current-Gain - Bandwidth Product

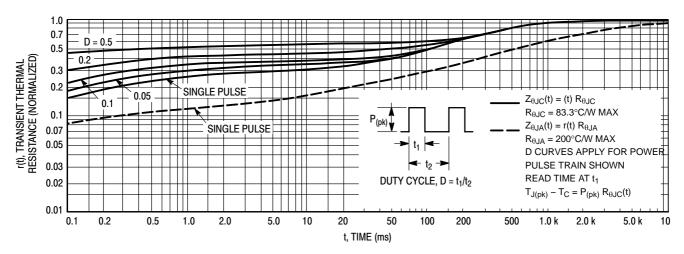


Figure 13. Thermal Response

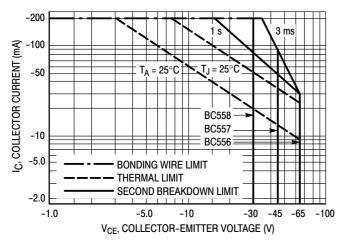


Figure 14. Active Region - Safe Operating Area

The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}C$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

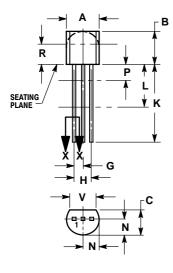
ORDERING INFORMATION

Device	Package	Shipping [†]
BC556BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC556BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557BRL1	TO-92	2000 / Tape & Reel
BC557BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC557BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC557CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC557CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC558BRLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC558BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

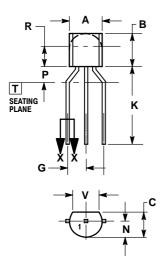


STRAIGHT LEAD **BULK PACK**



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17:

COLLECTOR PIN 1.

BASE

EMITTER

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